Wafer Cleaning

(BOE Etch)

- Rinse a new (100) orientation wafer under DI H$_2$O (> 18 MΩ) for a few seconds to wet the surface
- Completely submerge the wafer in the buffered oxide etch (BOE) for 180 seconds

CAUTION – BOE contains Hydrofluoric Acid (HF) in a surfactant and will cause severe burns to tissue.

- Remove the wafer from the BOE bath and rinse it well with DI H$_2$O for at least 30 seconds or more. The wafer should be very hydrophobic and water should easily run off of the surface.
- Blow-dry the wafer with N$_2$ gas